

4.3V to 18V Input, 2.0-A Synchronous Step-Down Converter with Fast Transient Response

Features

- 2.0-A Output Current
- High Efficient Integrated FETs Optimized for portable application:
95m Ω (High side) and 90m Ω (Low side)
- High Efficiency
Up to 95% Efficiency @ 5V Input, 3.3V Output
Up to 93% efficiency @ 12V Input, 3.3V Output
- Wide Input Voltage Range: 4.3V to 18V @ 2.0-A loading
- Wide Output Voltage Range: 0.918V to 14V @ 2.0-A loading (32Watt output @max)
- Low Output Ripple and Allows Ceramic Output Capacitor
- Thermal Shutdown Protection
- 340-KHz Switching Frequency(fsw)
- Cycle By Cycle Over Current Limit
- +/-1.5% High Accuracy Feedback Voltage

Applications

- Wide Range of Applications for Low Voltage System
- Digital TV Power Supply
- High Definition Blu-ray Disc Players
- Networking Home Terminal
- Digital STB
- Ideal for Portable Applications

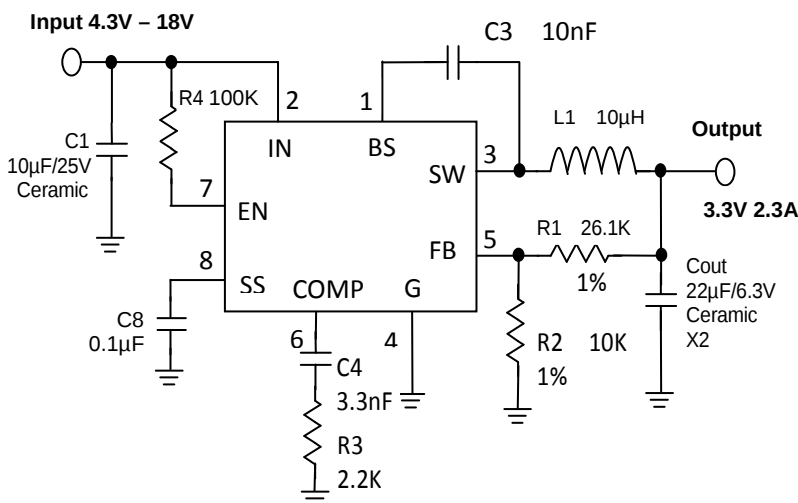
Descriptions

The BLI9182 is a current mode synchronous buck converter, and has a proprietary W-mode™ Gm curvature circuit that enables fast transient response, enables the device to adopt to both low ESR output capacitors, such as POSCAP or SP-CAP, and ultra-low ESR ceramic capacitors.

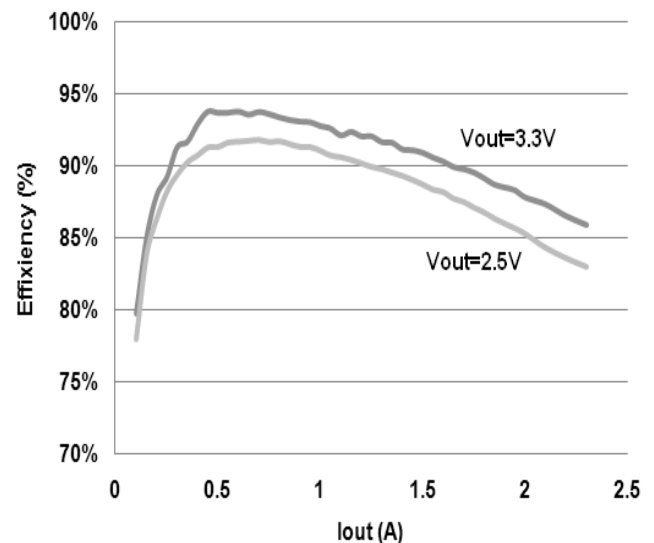
The BLI9182 operates from 4.3-V to 18-V Vin input, and the output voltage can be programmed between 0.918V to 14v with 2.0A output current, and +/-1.5% high accuracy output voltage.

Due to 95m Ω (High side) and 90m Ω (Low side) integrated FETs, the BLI9182 works in high efficiency (up to 94% @12V Input, 3.3V output) .

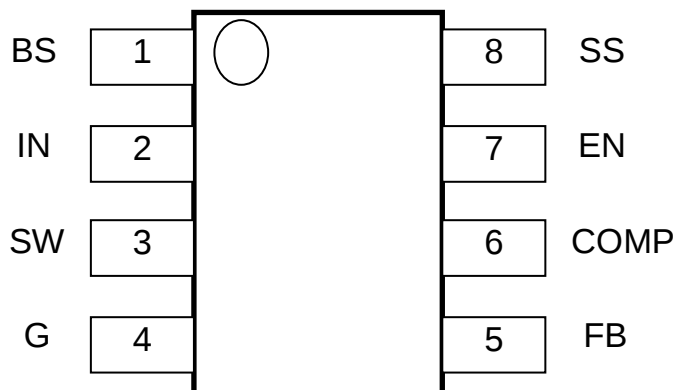
Typical Application



Efficiency vs. Iout @Vin=12v, L=15uH



PIN ARRANGEMENT



PIN FUNCTIONS

PIN		Description
NAME	NO.	Deatails
BS	1	Supply input for high-side NFET gate driver (boost terminal). Connect capacitor from this pin to SW pin. An internal PN diode is connected between VREG to BS pin.
IN	2	Power input and connected to high side NFET drain
SW	3	Switch node connection between high-side NFET and low-side NFET. Also serve as inputs to current comparators.
G	4	Signal ground pin, also serve as ground returns for low-side NFET.
FB	5	Converter feedback input. Connect with feedback resistor divider.
COMP	6	Compensation Node. Used to compensate control loop. Connect a series RC network from COMP to G. In some cases, an additional capacitor is required
EN	7	Enable control input
SS	8	Soft-start control. A external capacitor should be connected to G.

ABOSOLUTE MAXIMUM RATINGS

Over operating free-air temperature range (unless otherwise noted)

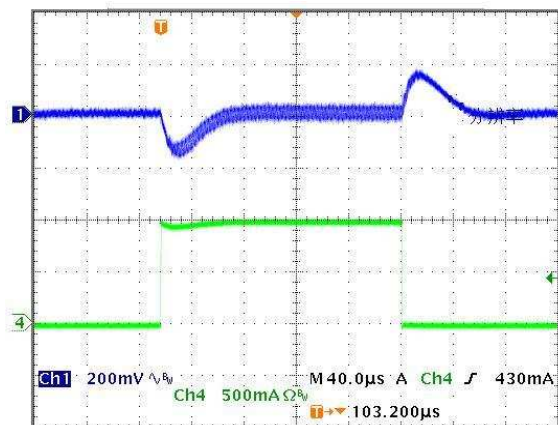
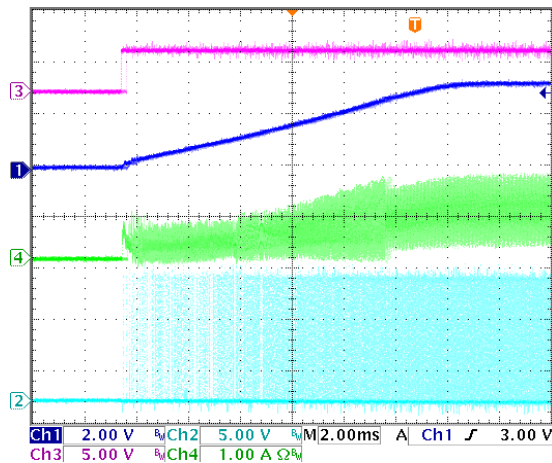
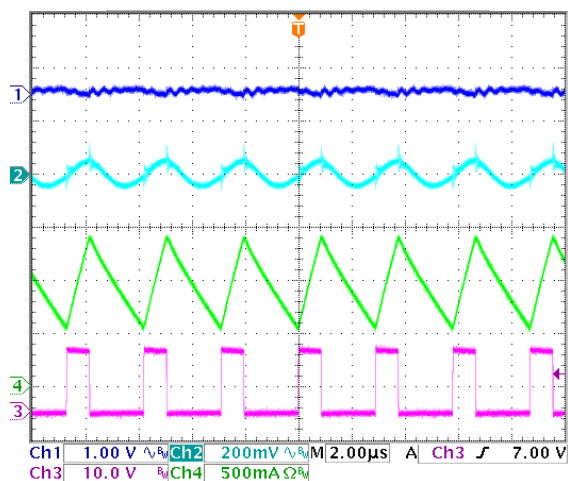
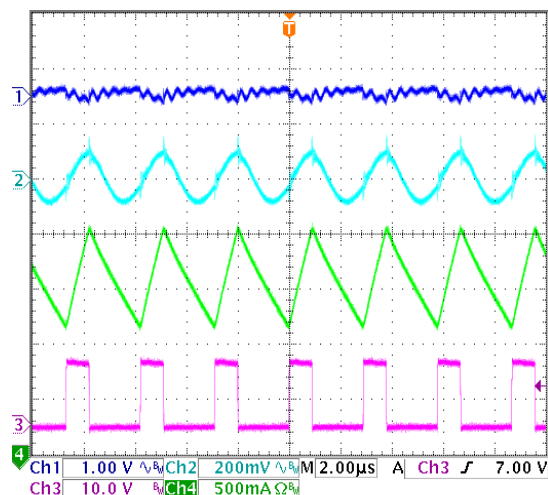
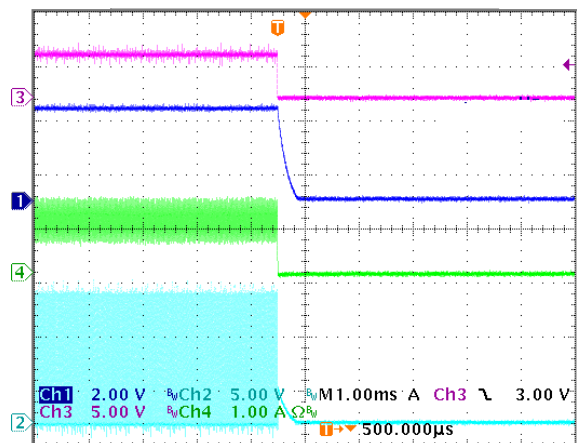
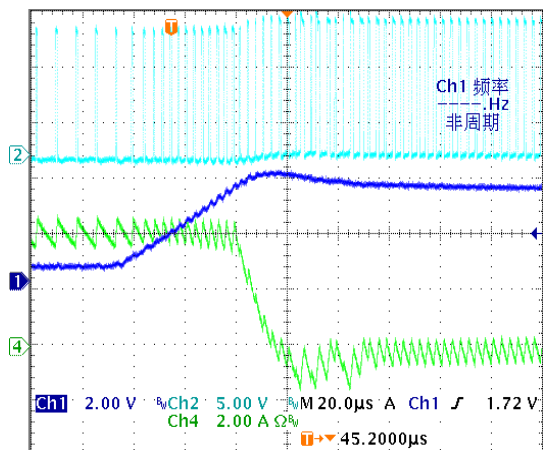
ITEMS	NAME	VALUE	UNIT
Voltage Range	IN	-0.3 to 20	V
	BS	-0.3 to 25	V
	SW	-2 to 20	V
	SW (10 ns transient)	-2.5 to 21	V
	FB,SS,COMP	-0.3 to 5.5	V
	EN	-0.3 to 8	V
TJ	Operation Junction	-40 to +150	°C
Tstg	Storage temperature	-55 to +150	°C

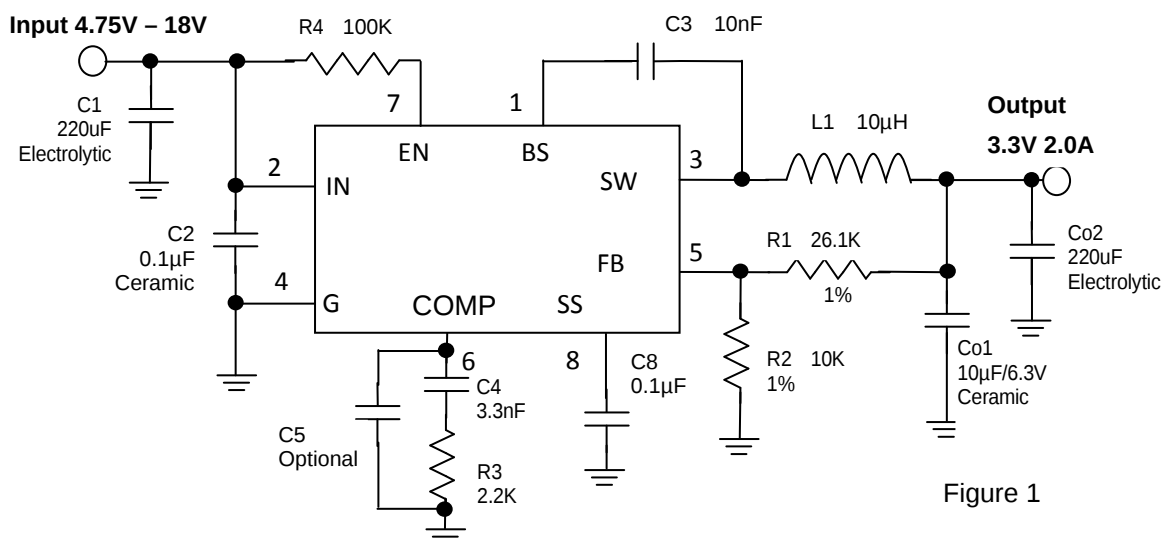
ELECTRICAL CHARACTERISTICS

Over operating free-air temperature range(unless otherwise noted)

VIN=12V, TA=25℃

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Supply Current						
Iin	Operating-non-switching supply current	VIN current, TA=25℃, EN=1.8V, VFB=1.0V		1.3	2.0	mA
ISDN	Shut Down Supply Current	VEN=0V		2	4	μA
VFB	Feedback Voltage	4.3V ≤VIN≤18V	0.900	0.923	0.946	V
OVP	Feedback Overvoltage Threshold			1.1		V
Aea	Error Amplifier Voltage Gain			1000		V/V
Gea	Error Amplifier Transconductance	△IC=+/-10μA		900		μA/V
RDS(on)_1	High Side Switch ON Resistance			95		mΩ
RDS(on)_2	Low Side Switch ON Resistance			90		mΩ
Ileakgae	High Side Switch Leakage Current	VEN=0V, VSW=0V			10	μA
ILM_H	High Side Switch Current Limit	Minimum Duty Cycle	2.8	3.5		A
ILM_L	Low Side Switch Current Limit	From Drain to Source		1.0		A
Gcs	COMP Voltage to Current Sense Transconductance			3.5		A/V
Fsw_1	Switching Frequency			340		KHz
Fsw_2	Short Circuit Switching Frequency	VFB=0V		100		KHz
Dmax	Maximum Duty Cycle	VFB=1.0V		90		%
TON_min	Minimum ON Time			220		ns
VEN_1	EN Threshold Voltage	VEN Rising	1.1	1.5	2.0	V
VHys_1	EN Threshold voltage's Hysteresis			100		mV
VEN_2	EN Lockout Threshold Voltage		1.8	2.0	2.2	V
VHys_2	EN Lockout Hysteresis			210		mV
VUVLO	Input Under Voltage Lockout Threshold	VIN Rising	3.0	3.6	4.2	V
VHys_3	Input Under Voltage Lockout Threshold Hysteresis			600		mV
Iss	Soft-Start Current	Vss=0V	4.25	4.40	4.55	μA
VFB-SS	Setting Feedback Voltage by Using Soft-Start Voltage	Only when Vss < 0.85V by adding resistor on SS pin Vss= Iss*Rss=4.40μA*Rss		Vss+30mV		
Tss	Soft-Start Period	Css=0.1μF		15		ms
TSD	Thermal Shutdown			160		℃

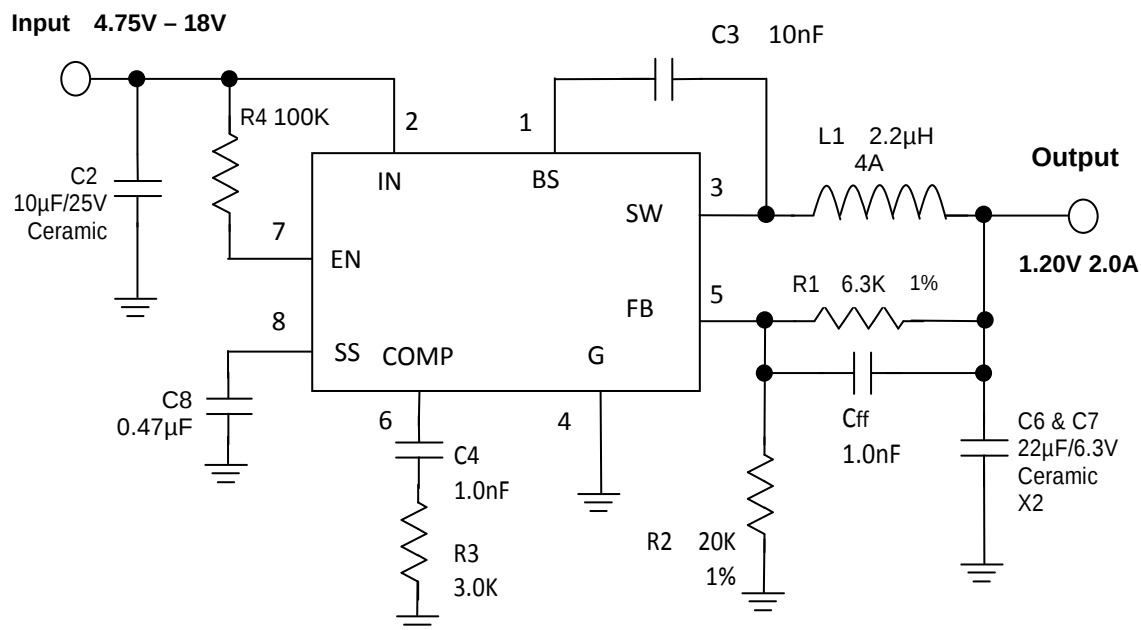
TYPICAL PERFORMANCE CHARACTERISTICS
 $V_{in}=12V, V_{out}=3.3V, L=10\mu H, C_{in}=10\mu F, C_{out}=22\mu F, T_A=+25^{\circ}C$
Fast Transient Response (20A/ μ s)

Startup through Enable

1A Load Operation

2A Load Operation

Shutdown through Enable

Short Circuit Recovery


APPLICATION SCHEMATIC (1)
1) With Electrolytic Capacitor


Compatible with main competitors without any external component change!

RECOMMENDED COMPONENT SELECTION

Vout	Cout	R1	R2	R3 (comp)	C4 (comp)	C5 (optional)	L(inductor)
1.0V	22μF Ceramic X2	1.0K	10K	50 Ω	10nF	OPEN	3.3μH
1.2V	22μF Ceramic X2	4.7K	15K	100 Ω	10nF	OPEN	3.3μH
1.8V	22μF Ceramic X2	9.7K	10K	300 Ω	3.3nF	OPEN	4.7μH
2.5V	22μF Ceramic X2	12.0K	6.8K	1.5K Ω	3.3nF	OPEN	6.8μH
3.3V	22μF Ceramic X2	26.1K	10K	2.2K Ω	3.3nF	OPEN	10μH
5.0V	22μF Ceramic X2	30.0K	6.8K	2.7K Ω	3.3nF	OPEN	22μH
1.0V	47μF SP Cap	1.0K	10K	50 Ω	10nF	OPEN	3.3μH
1.2V	47μF SP Cap	4.7K	15K	100 Ω	10nF	OPEN	3.3μH
1.8V	47μF SP Cap	9.7K	10K	300 Ω	3.3nF	OPEN	4.7μH
2.5V	47μF SP Cap	12.0K	6.8K	1.5K Ω	3.3nF	OPEN	6.8μH
3.3V	47μF SP Cap	26.1K	10K	2.2K Ω	3.3nF	OPEN	10μH
5.0V	47μF SP Cap	30.0K	6.8K	2.7K Ω	3.3nF	OPEN	22μH
1.0V	470μF/6.3V/Electrolytic	1.0K	10K	50 Ω	10nF	150pF	3.3μH
1.2V	470μF/6.3V/Electrolytic	4.7K	15K	100 Ω	10nF	150pF	3.3μH
1.8V	470μF/6.3V/Electrolytic	9.7K	10K	300 Ω	3.3nF	150pF	4.7μH
2.5V	470μF/6.3V/Electrolytic	12.0K	6.8K	1.5K Ω	3.3nF	150pF	6.8μH
3.3V	470μF/6.3V/Electrolytic	26.1K	10K	2.2K Ω	3.3nF	150pF	10μH
5.0V	470μF/10V/Electrolytic	30.0K	6.8K	2.7K Ω	3.3nF	150pF	22μH
12V	470μF/25V/Electrolytic	62.0K	5.1K	3.3K Ω	3.3nF	150pF	47μH

APPLICATION SCHEMATIC (2)
2) Fast Transient Response Without Electrolytic Capacitor

Figure 2
RECOMMENDED COMPONENT SELECTION

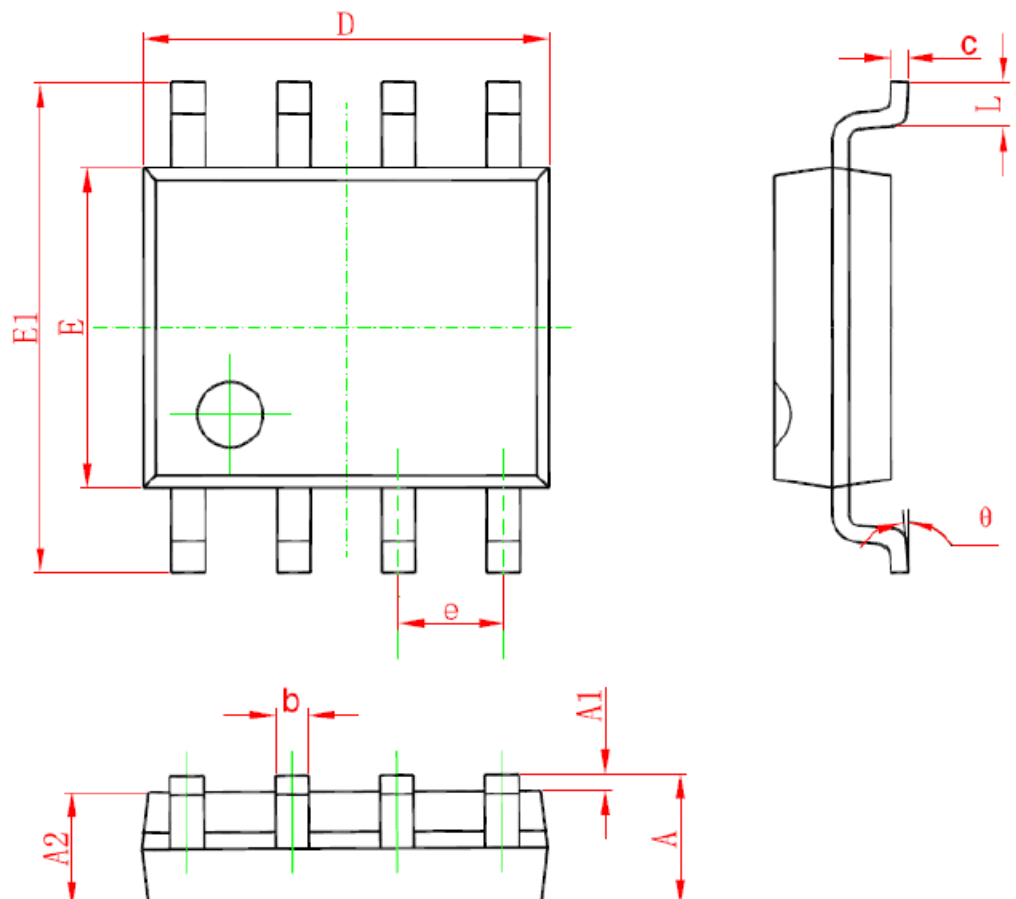
Vout	Cout	R1	R2	R3 (comp)	C4 (comp)	Cff	L inductor)
1.0V	22µF Ceramic X2	2.0K	20K	3.0K Ω	1.0nF	2.2nF	2.2µH
1.2V	22µF Ceramic X2	6.3K	20K	3.0K Ω	1.0nF	1.0nF	2.2µH
1.8V	22µF Ceramic X2	19.4K	20K	3.0K Ω	1.0nF	680pF	3.3µH
2.5V	22µF Ceramic X2	34.5K	20K	3.0K Ω	1.0nF	680pF	4.7µH
3.3V	22µF Ceramic X2	52.2K	20K	3.0K Ω	1.0nF	680pF	6.8µH
5.0V	22µF Ceramic X2	89.5K	20K	3.0K Ω	1.0nF	390pF	22µH
1.0V	47µF SP Cap	2.0K	20K	3.0K Ω	1.0nF	2.2nF	2.2µH
1.2V	47µF SP Cap	6.3K	20K	3.0K Ω	1.0nF	1.0nF	2.2µH
1.8V	47µF SP Cap	19.4K	20K	3.0K Ω	1.0nF	680pF	3.3µH
2.5V	47µF SP Cap	34.5K	20K	3.0K Ω	1.0nF	680pF	4.7µH
3.3V	47µF SP Cap	52.2K	20K	3.0K Ω	1.0nF	680pF	6.8µH
5.0V	47µF SP Cap	89.5K	20K	3.0K Ω	1.0nF	390pF	22µH

APPLICATION NOTES

- a) C2 ceramic 电容尽量靠近芯片的 PIN2 和 PIN4 放置;
- b) 使用 47 μ H 电感时, 由于每次 switching 传输的能量大, 输出需要更大的电容, 以使大信号的反馈环路稳定。使用 47 μ H 电感时, 输出须用大于或等于 330 μ F 的电解电容作能量 Bulk。
- c) 大电流路径尽量短, 且尽量与芯片在同一 PCB 层次。避免大电流路径打过孔跨层连接。
- d) 若成本可行, 在高效率设计中, 应尽量使用瓷片电容或较小 ESR (如: 30mohm) 的电解电容, 效率可有效提升 1%。
- e) EN 脚 (第 7 脚) 上拉电阻要求不低于 100K 欧。
- f) 若多个芯片共享同一输入电容, 需调节第 8 脚软起动电容的电容值分时延迟启动各芯片, 以避免多个芯片同时启动对电源输入电容产生冲击。延迟时间: 每 100nF 电容延迟 15ms。

PACKAGE INFORMATION

Package	SOP8	Devices per Tube	100	Unit	mm
		Devices per reel	2500		



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°		8°	